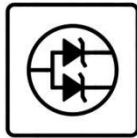


# MSKSEMI

SEMICONDUCTOR



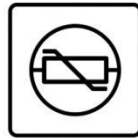
ESD



TVS



TSS



MOV

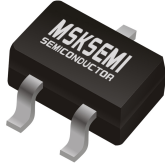


GDT

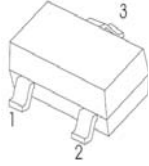


PLED

Product data sheet



SOT - 23



- 1. BASE
- 2. EMITTER
- 3. COLLECTOR

TRANSISTOR (NPN)

**FEATURES**

- Complementary to MMBT5401-MS
- Ideal for Medium Power Amplification and Switching

MARKING: G1

**MAXIMUM RATINGS (T<sub>a</sub>=25°C unless otherwise noted)**

Symbol	Parameter	Value	Unit
V <sub>CB0</sub>	Collector-Base Voltage	180	V
V <sub>CEO</sub>	Collector-Emitter Voltage	160	V
V <sub>EBO</sub>	Emitter-Base Voltage	6	V
I <sub>C</sub>	Collector Current	600	mA
P <sub>C</sub>	Collector Power Dissipation	300	mW
R <sub>θJA</sub>	Thermal Resistance From Junction To Ambient	416	°C/W
T <sub>J</sub> , T <sub>stg</sub>	Operation Junction and Storage Temperature Range	-55~+150	°C

**ELECTRICAL CHARACTERISTICS (T<sub>a</sub>=25°C unless otherwise specified)**

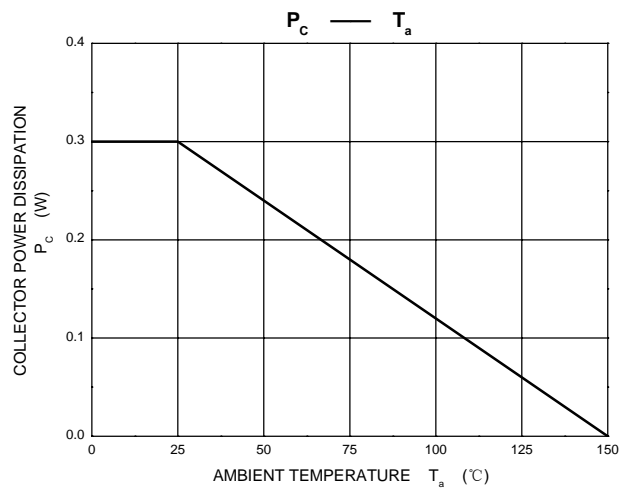
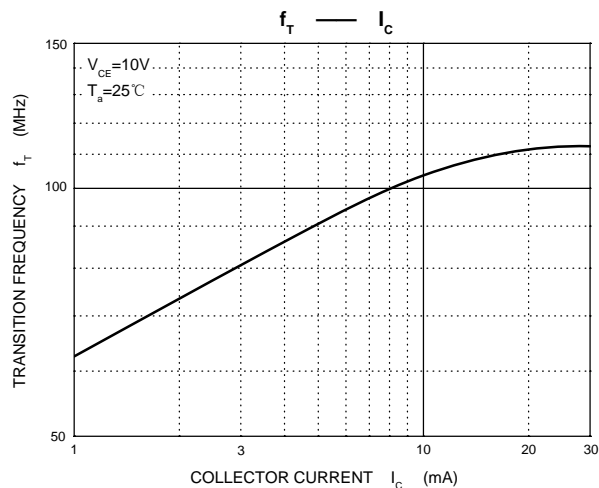
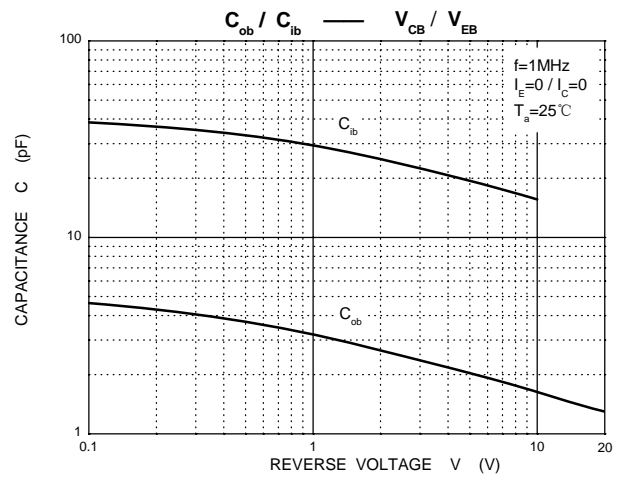
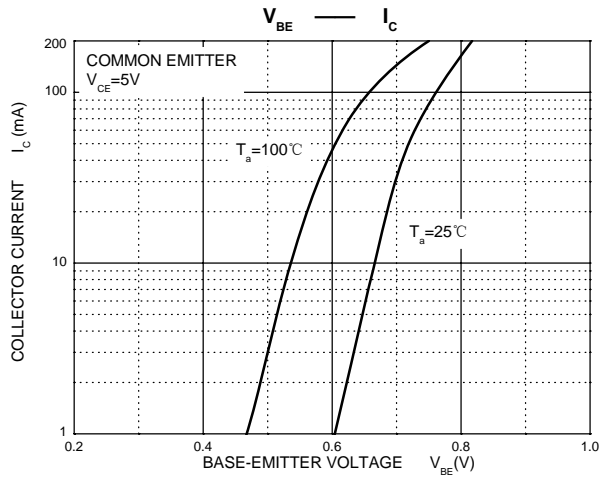
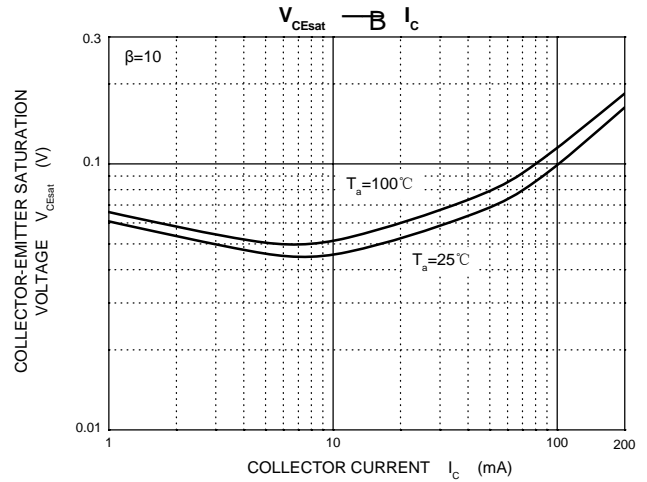
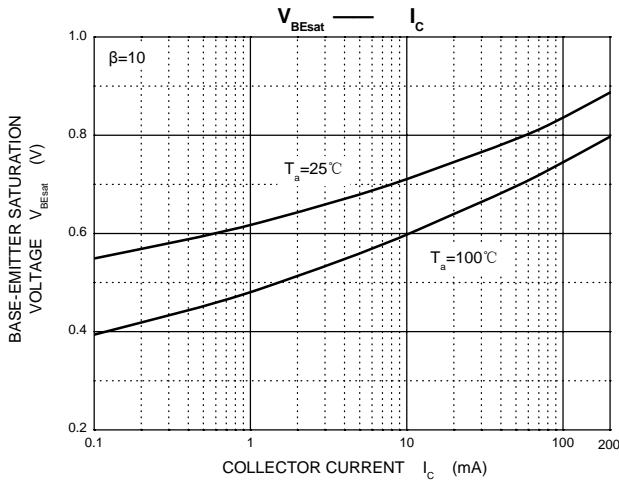
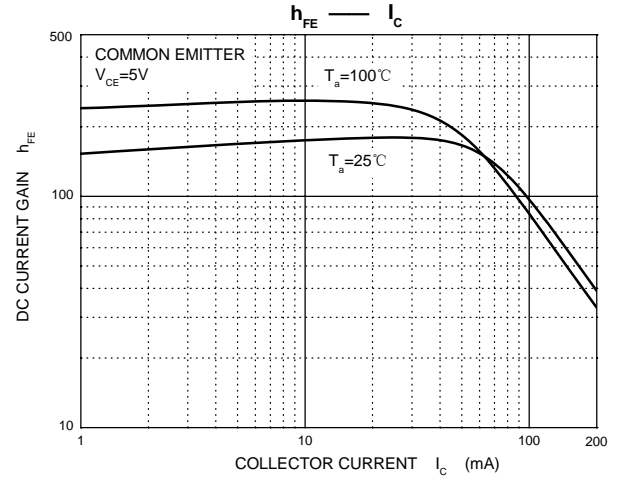
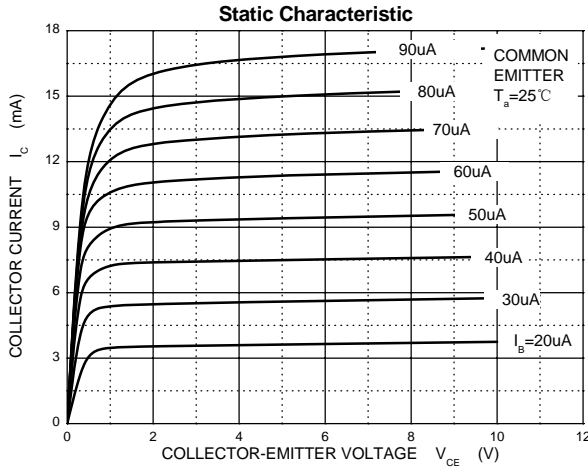
Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V <sub>(BR)CBO</sub>	I <sub>C</sub> =100μA, I <sub>E</sub> =0	180			V
Collector-emitter breakdown voltage	V <sub>(BR)CEO</sub> *	I <sub>C</sub> =1mA, I <sub>B</sub> =0	160			V
Emitter-base breakdown voltage	V <sub>(BR)EBO</sub>	I <sub>E</sub> =10μA, I <sub>C</sub> =0	6			V
Collector cut-off current	I <sub>CBO</sub>	V <sub>CB</sub> =120V, I <sub>E</sub> =0			50	nA
Emitter cut-off current	I <sub>EBO</sub>	V <sub>EB</sub> =4V, I <sub>C</sub> =0			50	nA
DC current gain	h <sub>FE(1)</sub> *	V <sub>CE</sub> =5V, I <sub>C</sub> =1mA	80			
	h <sub>FE(2)</sub> *	V <sub>CE</sub> =5V, I <sub>C</sub> =10mA	100		300	
	h <sub>FE(3)</sub> *	V <sub>CE</sub> =5V, I <sub>C</sub> =50mA	50			
Collector-emitter saturation voltage	V <sub>CE(sat)1</sub> *	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA			0.15	V
	V <sub>CE(sat)2</sub> *	I <sub>C</sub> =50mA, I <sub>B</sub> =5mA			0.2	V
Base-emitter saturation voltage	V <sub>BE(sat)1</sub> *	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA			1	V
	V <sub>BE(sat)2</sub> *	I <sub>C</sub> =50mA, I <sub>B</sub> =5mA			1	V
Transition frequency	f <sub>T</sub>	V <sub>CE</sub> =10V, I <sub>C</sub> =10mA, f=100MHz	100		300	MHz
Collector output capacitance	C <sub>ob</sub>	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz			6	pF

\*Pulse test: pulse width ≤300μs, duty cycle ≤ 2.0%.

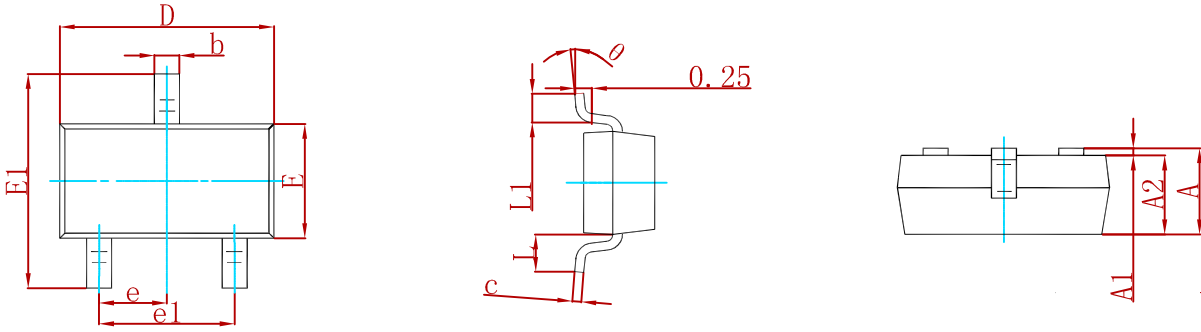
**CLASSIFICATION OF h<sub>FE(2)</sub>**

RANK	L	H
RANGE	100-200	200-300

Typical Characteristics

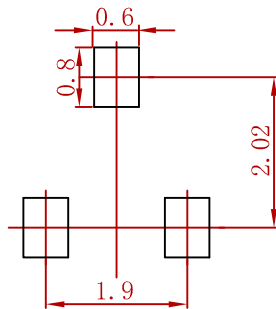


**PACKAGE MECHANICAL DATA**



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

**Suggested Pad Layout**



- Note:
1. Controlling dimension: in millimeters.
  2. General tolerance: ± 0.05mm.
  3. The pad layout is for reference purposes only.

**REEL SPECIFICATION**

P/N	PKG	QTY
MMBT5551-MS	SOT-23	3000

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